July 2000

DS96F173M/DS96F175C/DS96F175M EIA-485/EIA-422 Quad Differential Receivers



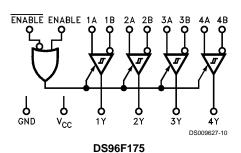
DS96F173M/DS96F175C/DS96F175M EIA-485/EIA-422 Quad Differential Receivers

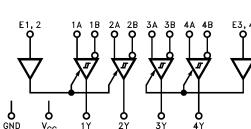
General Description

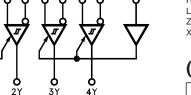
The DS96F173 and the DS96F175 are high speed quad differential line receivers designed to meet the EIA-485 standard. The DS96F173 and the DS96F175 offer improved performance due to the use of L-FAST bipolar technology. The use of LFAST technology allows the DS96F173 and DS96F175 to operate at higher speeds while minimizing power consumption.

The DS96F173 and the DS96F175 have TRI-STATE® outputs and are optimized for balanced multipoint data bus transmission at rates up to 15 Mbps. The receivers feature high input impedance, input hysteresis for increased noise immunity, and input sensitivity of 200 mV over a common mode input voltage range of -7V to +12V. The receivers are therefore suitable for multipoint applications in noisy environments. The DS96F173 features an active high and active low Enable, common to all four receivers. The DS96F175 features separate active high Enables for each receiver pair.

Logic Diagrams







4Y

DS009627-11

Features

- Meets EIA-485, EIA-422A, EIA-423A standards
- Designed for multipoint bus applications
- **TRI-STATE** outputs
- Common mode input voltage range: -7V to +12V
- Operates from single +5.0V supply
- Reduced power consumption ($I_{CC} = 50 \text{ mA max}$)
- Input sensitivity of ±200 mV over common mode range
- Input hysteresis of 50 mV typical
- High input impedance
- Military temperature range available
- Qualified for MIL STD 883C
- Available to standard military drawings (SMD)
- Available in DIP(J), LCC(E), and FlatPak (W) packages DS96F173 and DS96F175 are lead and function compatible with SN75173/175 or the

Function Tables

AM26LS32/MC3486

(Each Receiver) DS96F173

Differential Inputs	Ena	able	Output
A–B	E	Ē	Y
$V_{ID} \ge 0.2V$	н	Х	Н
	X	L	н
$V_{ID} \leq -0.2V$	н	Х	L
	X	L	L
Х	L	Х	Z
Х	Х	Н	Z

H = High Level

L = Low Level

Z = High Impedance (off)

X = Don't Care

(Each Receiver) DS96F175

Differential Inputs	Enable	Output
A–B	E	Y
$V_{ID} \ge 0.2V$	н	Н
$V_{ID} \leq -0.2V$	Н	L
Х	L	Z

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0 1Y

V_{CC}

COMMERCIAL

Absolute Maximum Ratings (Note 2)

Specifications for the 883 version of this product are listed separately.

Storage Temperature Range (T _{STG})	–65°C to +175°C
Lead Temperature	
(Soldering, 60 sec.)	300°C
Max. Package Power Dissipation (Note	1) at 25°C
Ceramic DIP (J)	1500 mW
Supply Voltage	7.0V
Input Voltage, A or B Inputs	±25V
Differential Input Voltage	±25V
Enable Input Voltage	7.0V
Low Level Output Current	50 mA

Recommended Operating Conditions

	Min	Тур	Max	Units
Supply Voltage (V _{CC})				
DS96F175C	4.75	5.0	5.25	V
Common Mode Input Voltage (V _{CM})	-7		+12	V
Differential Input Voltage (V _{ID})			12	V
Output Current HIGH (I _{OH})			-400	μA
Output Current LOW (I _{OL})			11	mA
Operating Temperature (T_A)				
DS96F175C	0	25	70	°C
Note 1: Derate package 10 mW/°C above 25°C.				

Electrical Characteristics (Notes 3, 4)

Over recommended supply voltage and operating temperature ranges, unless otherwise specified

Symbol	Parameter	Con	ditions	Min	Тур	Max	Units	
V _{TH}	Differential-Input	V _O = V _{OH}	$V_{O} = V_{OH}$			0.2	V	
	High Threshold Voltage							
V _{TL}	Differential-Input (Note 5)	$V_{O} = V_{OL}$		-0.2			V	
	Low Threshold Voltage							
$V_{TH} - V_{TL}$	Hysteresis (Note 6)	$V_{CM} = 0V$			50		mV	
V _{IH}	Enable Input Voltage HIGH			2.0			V	
V _{IL}	Enable Input Voltage LOW					0.8	V	
V _{IC}	Enable Input Clamp Voltage	I _I = -18 mA				-1.5	V	
V _{он}	Output Voltage HIGH	V _{ID} = 200 mV	0°C to +70°C	2.8			v	
		I _{OH} = -400 μA	–55°C to +125°C	2.5			v	
V _{OL}	Output Voltage LOW	V _{ID} = -200 mV	I _{OL} = 8.0 mA			0.45	V	
			I _{OL} = 11 mA			0.50	V	
l _{oz}	High-Impedance State Output	$V_{\rm O} = 0.4$ V to 2.4V				±20	μA	
I _I	Line Input Current (Note 7)	Other Input = 0V	V ₁ = 12V			1.0	mA	
			$V_1 = -7.0V$			-0.8		
I _{IH}	Enable Input Current HIGH	V _{IH} = 2.7V				20	μA	
IIL	Enable Input Current LOW	$V_{IL} = 0.4V$				-100	μA	
R _I	Input Resistance			14	18	22	kΩ	
l _{os}	Short Circuit Output Current	(Note 8)		-15		-85	mA	
I _{cc}	Supply Current	No Load	Outputs Enabled			50	~ ^	
I _{ccx}	7		Outputs Disabled			50	mA	

COMMERCIAL Switching Characteristics $V_{CC} = 5.0V$, $T_A = 25^{\circ}C$

Symbol	Parameter	Conditions	Min	Тур	Max	Units
t _{PLH}	Propagation Delay Time,	$V_{ID} = -2.5V \text{ to } +2.5V,$	5.0	15	22	ns
	Low to High Level Output	$C_L = 15 \text{ pF}, Figure 1$				
t _{PHL}	Propagation Delay Time,	$V_{CM} = 0V$	5.0	15	22	ns
	High to Low Level Output					
t _{zH}	Output Enable Time to High Level	C _L = 15 pF, <i>Figure 2</i>		12	16	ns
t _{ZL}	Output Enable Time to Low Level	C _L = 15 pF, <i>Figure 3</i>		13	18	ns
t _{HZ}	Output Disable Time from High Level	C _L = 5.0 pF, <i>Figure 2</i>		14	20	ns

Switching Characteristics (Continued)

$V_{CC} = 5.0V, T_A = 25^{\circ}C$

Symbol	Parameter	Conditions	Min	Тур	Max	Units
t _{LZ}	Output Disable Time from Low Level	C _L = 5.0 pF, <i>Figure 3</i>		14	18	ns
t _{PLH} -t _{PHL}	Pulse Width Distortion (SKEW)	Figure 1		1.0	3.0	ns

Note 2: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" provide conditions for actual device operation.

Note 3: Unless otherwise specified min/max limits apply across the 0°C to +70°C range for the DS96F175C. All typicals are given for $V_{CC} = 5V$ and $T_A = 25°C$. **Note 4:** All currents into the device pins are positive; all currents out of the device pins are negative. All voltages are reference to ground unless otherwise specified. **Note 5:** The algebraic convention, when the less positive (more negative) limit is designated minimum, is used in this data sheet for common mode input voltage and threshold voltage levels only.

Note 6: Hysteresis is the difference between the positive-going input threshold voltage. V_{TH}, and the negative going input threshold voltage, V_{TL}.

Note 7: Refer to EIA-485 Standard for exact conditions.

Note 8: Only one output at a time should be shorted.

Order Number: DS96F175CJ

See NS Package Number J16A

MIL-STD-883C

Absolute Maximum Ratings (Note 2)

For complete Military Specifications, refer to the appropriate SMD or MDS.

Storage Temperature Range (T _{STG})	–65°C to +175°C
Lead Temperature (Soldering, 60 sec.)	300°C
Max. Package Power Dissipation (Note 9)	at 25°C
Ceramic DIP (J)	1500 mW
Ceramic Flatpak (W)	1034 mW
Ceramic LCC (E)	1500 mW
Supply Voltage	7.0V
Input Voltage, A or B Inputs	±25V
Differential Input Voltage	±25V
Enable Input Voltage	7.0V
Low Level Output Current	50 mA

Recommended Operating Conditions

	Min	Тур	Max	Units
Supply Voltage (V _{CC})				
DS96F173M/DS96F175M	4.50	5.0	5.50	V
Common Mode Input Voltage (V _{CM})	-7		+12	V
Differential Input Voltage (VID)			12	V
Output Current HIGH (I _{OH})			-400	μA
Output Current LOW (I _{OL})			11	mA
Operating Temperature (T _A)				
DS96F173M/DS96F175M	-55	25	125	°C
Note 9: Above $T_A = 25^{\circ}C$ derate J p 6.90 mW/°C, E package 11.11 mW/°C.	ackage 10	mW/	°C, W	package

Electrical Characteristics (Notes 3, 4)

Over recommended supply voltage and operating temperature ranges, unless otherwise specified

Symbol	Parameter	Con	ditions	Min	Max	Units
V_{TH}	Differential-Input High Threshold Voltage	$V_{CC} = 4.5V, 5.5V$ $V_{CM} = 0V, 12V, -12V$	V		0.2	V
V_{TL}	Differential-Input (Note 5) Low Threshold Voltage	$V_{CC} = 4.5V, 5.5V$ $V_{CM} = 0V, 12V, -12V$	V	-0.2		V
V _{IH}	Enable Input Voltage HIGH			2.0		V
V _{IL}	Enable Input Voltage LOW				0.8	V
V _{IC}	Enable Input Clamp Voltage	$I_{I} = -18 \text{ mA}, V_{CC} = 4$	4.5V		-1.5	V
V _{OH}	Output Voltage HIGH	V _{ID} = 200 mV I _{OH} = -400 μA	–55°C to +125°C	2.5		V
V _{OL}	Output Voltage LOW	$V_{ID} = -200 \text{ mV}$	I _{OL} = 8.0 mA		0.45	V
l _{oz}	High-Impedance State Output	$V_{\rm O} = 0.4$ V, 2.4V, $V_{\rm C}$	$V_{\rm O} = 0.4$ V, 2.4V, $V_{\rm CC} = 5.5$ V		±20	μA
l _i	Line Input Current (Note 7)	Other Input = 0V	V _I = 12V		1.0	
			$V_{I} = -7.0V$		-0.8	mA
I _{IH}	Enable Input Current HIGH	V _{IH} = 2.7V, V _{CC} = 5.	5V		20	μA
I _{IL}	Enable Input Current LOW	$V_{IL} = 0.4V, V_{CC} = 5.$	5V		-100	μA
R _I	Input Resistance			10		kΩ
l _{os}	Short Circuit Output Current	(Note 8)		-15	-85	mA
I _{cc} I _{ccx}	Supply Current	No Load	Outputs Enabled or Disabled		50	mA

MIL-STD-883C Switching Characteristics

 $V_{\rm CC} = 5.0 V$ $T_A = -55^{\circ}C$ Symbol Parameter Conditions T_A = 25°C T_A = 125°C Units Max Тур Max Max $V_{ID} = -2.5V$ to +2.5V, t_{PLH} Propagation Delay Time, 15 22 30 30 ns Low to High Level Output $C_L = 15 \text{ pF}, Figure 1$ Propagation Delay Time, $V_{CM} = 0V$ 15 22 30 30 t_{PHL} ns High to Low Level Output Output Enable Time to High $C_L = 15 \text{ pF}, Figure 2$ 12 16 27 27 t_{zH} ns Level

T_A = 125°C Units $T_A = -55^{\circ}C$ Max Max 27 27 ns 27 27 ns 37 37 ns 30 30 ns 5.0 5.0 ns

SMD Number:	DS96F173MJ	5962-9076602 MEA
	DS96F173MW	5962-9076602 MFA
	DS96F173ME	5962-9076602 M2A
	DS96F175MJ	5962-9076601 MEA
	DS96F175MW	5962-9076601 MFA
	DS96F175ME	5962-9076601 M2A
Order Number:	883 Marking	SMD Marking
	DS96F173MJ/883	DS96F173MJ-SMD
	DS96F175MJ/883	DS96F175MJ-SMD
	See NS Package Number	
	J16A	
	DS96F173ME/883	DS96F173ME-SMD
	DS96F175ME/883	DS96F175ME-SMD
	See NS Package Number	
	E20A	
	DS96F173MW/883	DS96F173MW-SMD
	DS96F175MW/883	DS96F175MW-SMD
	See NS Package Number	
	W16A	
	For complete Military Product to the appropriate SMD or M	
	and the second of the	-

Conditions

C_L = 5.0 pF, *Figure 2*(Note 15)

 $C_L = 20 \text{ pF}, Figure 2(\text{Note 15})$

 $C_L = 15 \text{ pF}, Figure 3$

 $C_L = 5.0 \text{ pF}, Figure 3$

Figure 1

T_A = 25°C

Max

18

20

30

18

3

Тур

13

14

14

14

1

Switching Characteristics (Continued)

Parameter

Output Enable Time to Low

Output Disable Time from High

Output Disable Time from Low

Pulse Width Distortion (SKEW)

Level

Level

Level

 $V_{\rm CC} = 5.0V$

Symbol

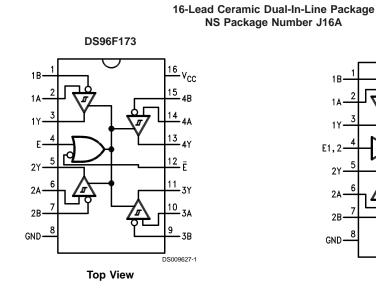
 t_{ZL}

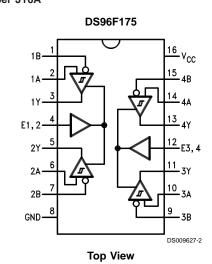
 t_{HZ}

 t_{LZ}

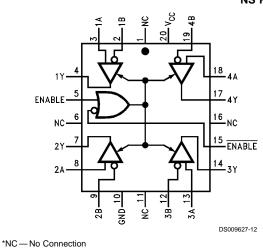
 $|t_{PLH} - t_{PHL}|$

Connection Diagrams





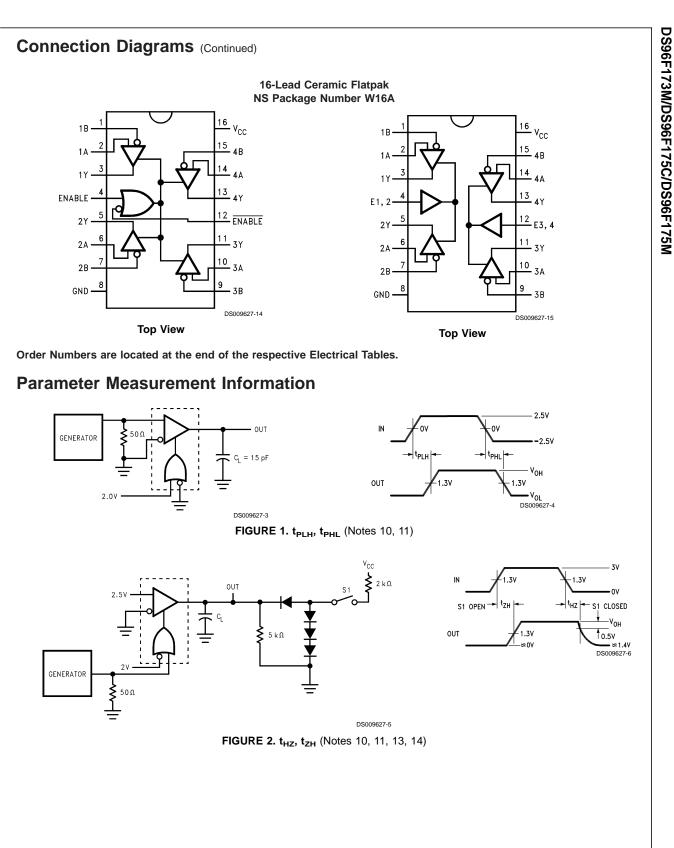
20-Lead Ceramic Leadless Chip Carrier NS Package Number E20A



S 18 **4**A 1 17 4Y E1,2 16 -NC NC 15 2Y E3.4 4 2A 28 GND 38. Ś 3Å. DS009627-13 **Top View**

Top View

DS96F173M/DS96F175C/DS96F175M



DS96F173M/DS96F175C/DS96F175M

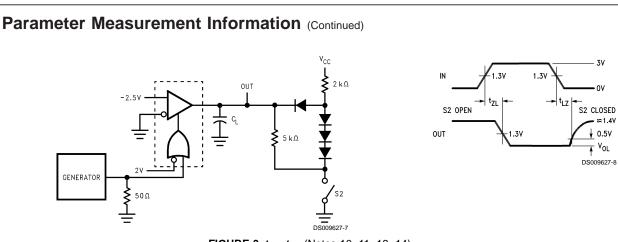


FIGURE 3. t_{ZL}, t_{LZ} (Notes 10, 11, 13, 14)

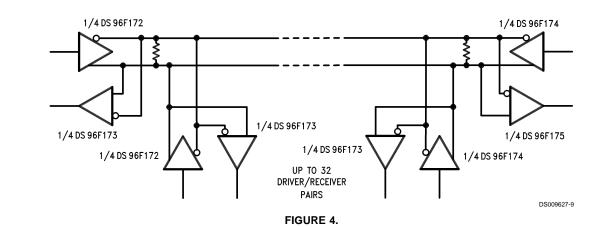
Note 10: The input pulse is supplied by a generator having the following characteristics: f = 1.0 MHz, 50% duty cycle, $t_r \le 6.0 \text{ ns}$, $t_f \le 6.0 \text{ ns}$, $Z_O = 50\Omega$. Note 11: C_L includes probe and stray capacitance.

Note 12: DS96F173 with active high and active low Enables are shown. DS96F175 has active high Enable only.

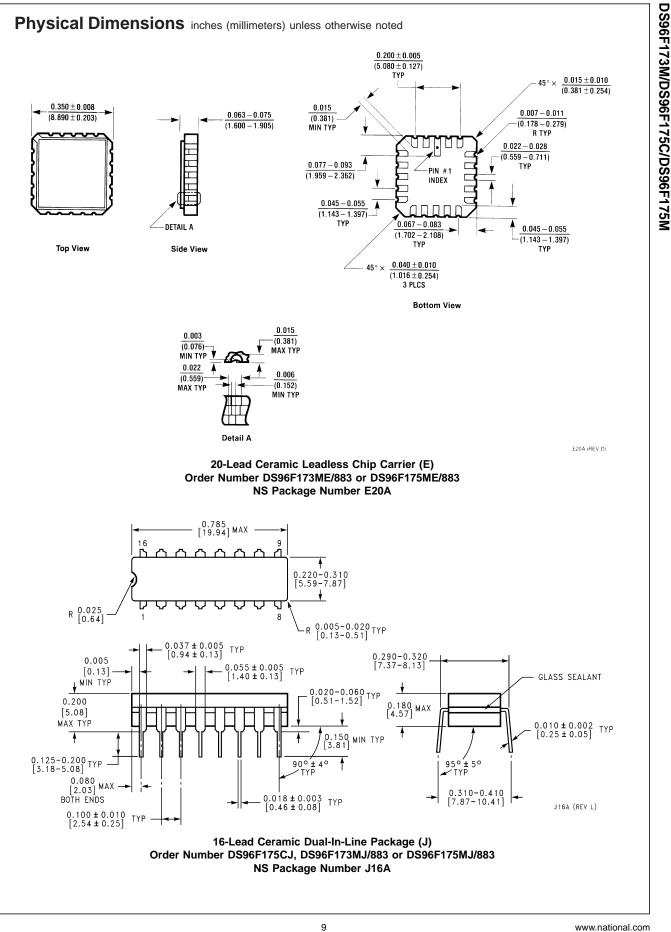
Note 13: All diodes are 1N916 or equivalent.

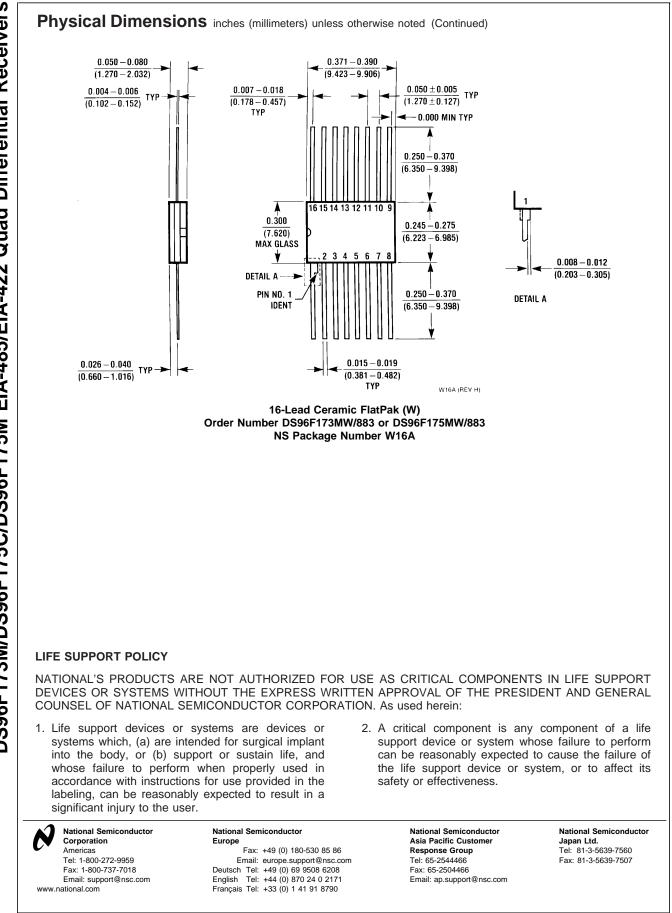
Note 14: To test the active low Enable \overline{E} of DS96F173, ground E and apply an inverted input waveform to \overline{E} . DS96F175 has active high enable only. **Note 15:** Testing at 20 pF assures conformance to 5 pF specification.

Typical Application



Note: The line length should be terminated at both ends in its characteristic impedance. Stub lengths off the main line should be kept as short as possible.





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